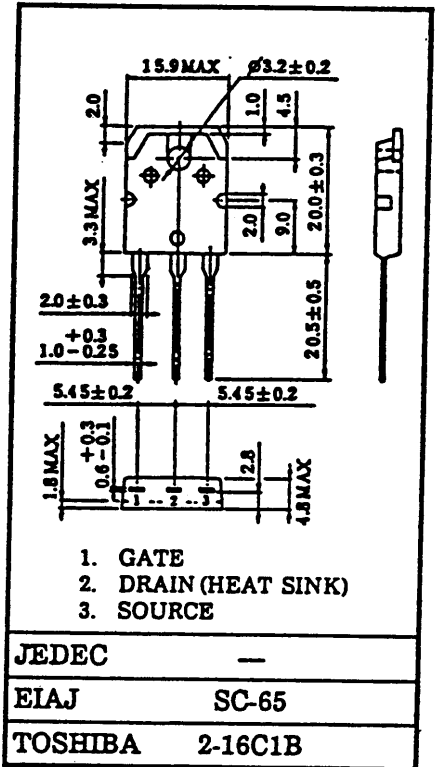


TOSHIBA FIELD EFFECT TRANSISTOR 2SK2150 SILICON N CHANNEL MOS TYPE (π - MOS IV)

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS.
CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR
DRIVE APPLICATIONS.

INDUSTRIAL APPLICATIONS
UNIT in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 0.29\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 14 S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100 \mu A$ (Max.) ($V_{DS} = 500V$)
- Enhancement-Mode : $V_{th} = 2.0 \sim 4.0V$ ($V_{DS} = 10V, I_D = 1mA$)



Weight : 4.6g

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	500	V
Drain-Gate Voltage ($R_{GS} = 20K\Omega$)	V_{DGR}	500	V
Gate-Source Voltage	V_{GSS}	± 30	V
Drain Current	DC	I_D	15 A
	Pulse	I_{DP}	60 A
Drain Power Dissipation ($T_c = 25^\circ C$)	P_D	150	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ C$

THERMAL CHARACTERISTICS

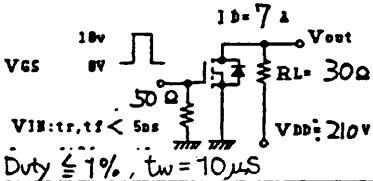
CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel To Case	$R_{th(ch-c)}$	0.833	$^\circ C/W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	50	$^\circ C/W$

THIS TRANSISTOR IS AN ELECTROSTATIC SENSITIVE DEVICE. PLEASE HANDLE WITH CAUTION.

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TOSHIBA CORPORATION

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		IGSS	VGS= ±25V, VDS= 0V	—	—	±10	μA
Gate-Source Breakdown Voltage		V (BR) GSS	IG= ±100 μA, VDS= 0V	±30	—	—	
Drain Cut-off Current		IDSS	VDS= 500V, VGS= 0V	—	—	100	μA
Drain-Source Breakdown Voltage		V (BR) DSS	ID= 10mA, VGS= 0V	500	—	—	V
Gate Threshold Voltage		Vth	VDS= 10V, ID= 1mA	2.0	—	4.0	V
Drain-Source ON Resistance		RDS (ON)	VGS= 10V, ID= 7A	—	0.29	0.40	Ω
Forward Transfer Admittance		Yfs	VDS= 10V, ID= 7A	—	14	—	S
Input Capacitance		Ciss	VDS= 10V, VGS= 0V f= 1MHz	—	2350	—	pF
Reverse Transfer Capacitance		Crss		—	200	—	
Output Capacitance		Coss		—	730	—	
Switching Time	Rise Time	tr		—	20	—	nS
	Turn-on Time	ton		—	55	—	
	Fall Time	tf		—	40	—	
	Turn-off Time	toff		—	235	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Qg	VDD= 400V, VGS= 10V ID= 15A	—	50	—	nC
Gate-Source Charge		Qgs		—	30	—	
Gate-Drain ("Miller") Charge		Qgd		—	20	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	IDR	—	—	—	15	A
Pulse Drain Reverse Current	IDRP	—	—	—	60	A
Diode Forward Voltage	VDSF	IDR= 15A, VGS= 0V	—	—	-1.7	V
Reverse Recovery Time	trr	IDR= 15A, VGS= 0V dIDR/dt= 100A/μS	—	490	—	nS
Reverse Recovery Charge	Qrr		—	5.4	—	μC

